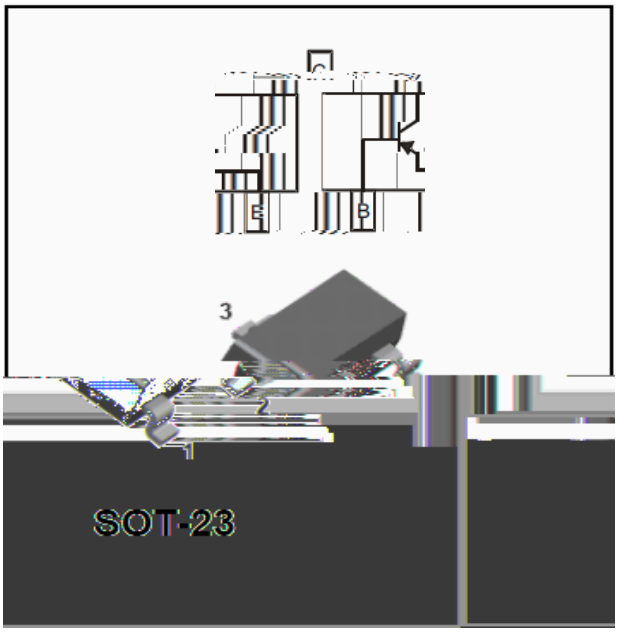
BC859C

PNP Transistor



Features

- Epoxy meets UL-94 V-0 flammability rating
- Halogen free available upon request by adding suffix ”HF”
- Moisture Sensitivity Level 1
- High Conductance
- Surface Mount Package Ideally Suited for Automatic Insertion

Mechanical Data

- **Package**: SOT-23
Molding compound meets UL 94 V-0 flammability rating, RoHS-compliant, halogen-free
- **Terminals:** Tin plated leads, solderable per J-STD-002 and JESD22-B102
- **Marking**: 4C

■ **Maximum Ratings** (Ta=25 unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-30	V
V_{CEO}	Collector-Emitter Voltage	-30	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current	-0.1	A
P_C	Collector Power Dissipation	200	mW
$R_{\Theta JA}$	Thermal Resistance From Junction To Ambient	625	/W
Tj	Junction Temperature	150	
T_{stg}	Storage Temperature	-55 +150	

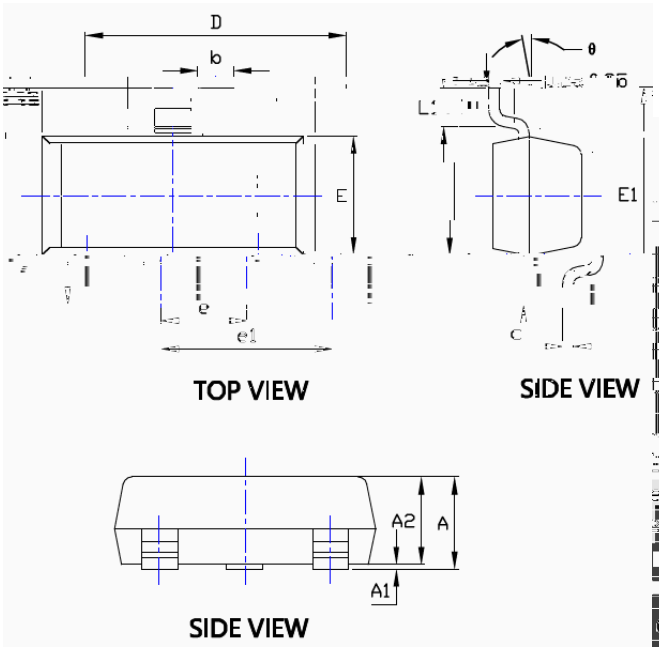
■ Electrical Characteristics (Ta=25 unless otherwise noted)

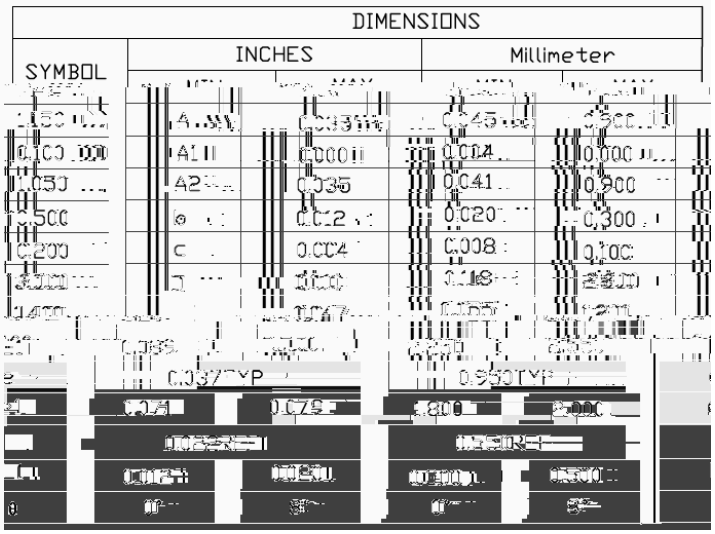
Parameter	Symbol	Test conditions	Min	Max	Unit
Collector-base breakdown voltage	V_{CBO}	I_C= -10μA, I_E=0	-30		V
Collector-emitter breakdown voltage	V_{CEO}	I_C= -10mA, I_B=0	-30		V
Emitter-base breakdown voltage	V_{EBO}	I_E= -1μA, I_C=0	-5		V
Collector-base cut-off current	I_{CBO}	V_{CB}=-30 V ,I_E=0		-0.1	μA
Emitter-base cut-off current	I_{EBO}	V_{EB}=-5 V , I_C=0		-0.1	μA
DC current gain	h_{FE}	V_{CE}= -5V, I_C= -2mA	420	800	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-100mA, I_B= -5mA		-0.65	V
Base-emitter saturation voltage	$V_{BE(sat)}$	I_C=-100mA, I_B= -5mA		-1.1	V
Transition frequency	f_T	V_{CE}= -5 V, I_C= -10mA f=100MHz	100		MHz
Collector-base output capacitance	Cob	VCB=-10V,f=1MHz		4.5	pF

■ Ordering Information (Example)

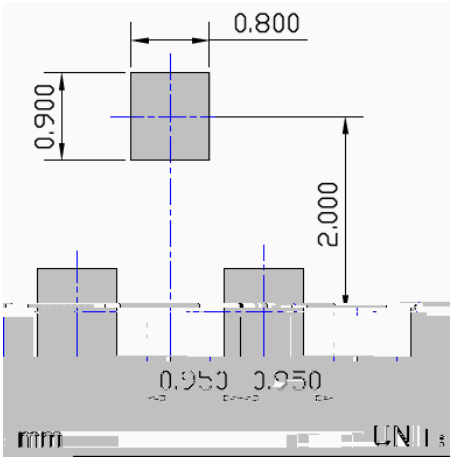
BC859C

■SOT-23 Package Outline Dimensions





■SOT-23 Soldering Footprint



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